

ABSTRACT

Provided is a method for producing a semiconductor substrate including a cleaning step of a semiconductor substrate, capable of removing (cleaning) an adhesive layer from a semiconductor substrate having the adhesive layer on a surface thereof more cleanly in a shorter time by a simple operation, a method for producing a processed semiconductor substrate including such a semiconductor production method, and a composition used in such a cleaning step.

A method for producing a semiconductor substrate, including a step of releasing and dissolving an adhesive layer on a semiconductor substrate using a releasing and dissolving composition, and cleaning the adhesive layer, in which the releasing and dissolving composition contains: a component [I]: a dissolution component containing a quaternary ammonium salt and an amide-based solvent, and a component [II]: a release component having a molecular weight of less than 160 and being composed of one or more solvents selected from an ether compound, a thioether compound, an aromatic hydrocarbon compound, an aliphatic hydrocarbon compound, an ester compound, and an amine compound, and a contact angle of the releasing and dissolving composition when the releasing and dissolving composition is added dropwise onto the adhesive layer

disposed on the semiconductor substrate is more than 22.6 degrees and less than 46.1 degrees.

[No figure]